

L Number	Hits	Search Text	DB	Time stamp
1	1533	buried near10 source near10 drain	USPAT; US-PGPUB	2003/03/06 17:02
2	2119	buried with source with drain	USPAT; US-PGPUB	2003/03/06 17:03
3	2119	(buried near10 source near10 drain) (buried with source with drain)	USPAT; US-PGPUB	2003/03/06 16:16
4	444	((buried near10 source near10 drain) (buried with source with drain)) and ((single mono) near3 crystal\$6)	USPAT; US-PGPUB	2003/03/06 17:03
9	661	buried near10 source near10 drain	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 17:03
10	1095	buried with source with drain	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 17:03
11	1095	(buried near10 source near10 drain) (buried with source with drain)	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 17:03
12	43	((buried near10 source near10 drain) (buried with source with drain)) and ((single mono) near3 crystal\$6)	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 17:03
-	495266	dielectric insulat\$3	USPAT; US-PGPUB	2002/09/07 19:26
-	87316	(dielectric insulat\$3) and gate	USPAT; US-PGPUB	2002/09/07 19:26
-	16217	((dielectric insulat\$3) and gate) and spacer	USPAT; US-PGPUB	2002/09/07 19:26
-	15506	((dielectric insulat\$3) and gate) and spacer) and (recess open\$3 hole via contact trench)	USPAT; US-PGPUB	2002/09/07 19:33
-	1634	((dielectric insulat\$3) and gate) and spacer) and (recess open\$3 hole via contact trench) and (isotropic\$5 near5 etch\$3)	USPAT	2002/09/07 19:27
-	241	((dielectric insulat\$3) and gate) and spacer) and (recess open\$3 hole via contact trench) and (isotropic\$5 near5 etch\$3)	US-PGPUB	2002/09/07 19:20
-	946251	dielectric insulat\$3	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:26
-	72774	(dielectric insulat\$3) and gate	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:26
-	3911	((dielectric insulat\$3) and gate) and spacer	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:26
-	2227	((dielectric insulat\$3) and gate) and spacer) and (recess open\$3 hole via contact trench)	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:27
-	48	((dielectric insulat\$3) and gate) and spacer) and (recess open\$3 hole via contact trench) and (isotropic\$5 near5 etch\$3)	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:31
-	48244	(source drain) same junction	USPAT; US-PGPUB	2002/09/07 19:59
-	1526	((source drain) same junction) and ((silicon near5 germanium) SiGe)	USPAT; US-PGPUB	2002/09/07 19:59
-	1446	((source drain) same junction) and ((silicon near5 germanium) SiGe)) and (recess open\$3 hole via contact trench)	USPAT; US-PGPUB	2002/09/07 19:34
-	1278	((source drain) same junction) and ((silicon near5 germanium) SiGe)) and (recess open\$3 hole via contact trench)	USPAT	2002/09/07 19:59
-	14097	(source drain) same junction	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:59
-	425	"19" and ((silicon near5 germanium) SiGe)	EPO; JPO; DERWENT; IBM_TDB	2002/09/07 19:59

-	97	("19" and ((silicon near5 germanium) SiGe)) and (recess open\$3 hole via contact trench) (spacer same (gate electrode))	EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB USPAT; US_PGPUB USPAT; US_PGPUB USPAT; US_PGPUB	2002/09/07 20:00 2003/03/06 11:54 2003/03/06 11:54 2003/03/06 11:54 2003/03/06 11:54 2003/03/06 11:54
-	26288			
-	3816	((spacer same (gate electrode))) and (anisotropic\$3 same etch\$3 same spacer)	EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB USPAT; US_PGPUB USPAT; US_PGPUB	2003/03/06 11:54 2003/03/06 11:54 2003/03/06 11:54
-	2013	((spacer same (gate electrode))) and (anisotropic\$3 same etch\$3 same spacer)) and ((recess open\$3 hole) same substrate)	USPAT; US_PGPUB	2003/03/06 11:54
-	76	((((spacer same (gate electrode))) and (anisotropic\$3 same etch\$3 same spacer)) and ((recess open\$3 hole) same substrate)) and ((dop\$4 same ((single mono) near3 crystal\$6)) same (recess open\$3 hole))	USPAT; US_PGPUB	2003/03/06 11:54
-	17277	(spacer same (gate electrode))	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 11:54
-	380	((spacer same (gate electrode))) and (anisotropic\$3 same etch\$3 same spacer)	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 11:54
-	1	((((spacer same (gate electrode))) and (anisotropic\$3 same etch\$3 same spacer)) and ((recess open\$3 hole) same substrate)) and ((dop\$4 same ((single mono) near3 crystal\$6)) same (recess open\$3 hole))	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 11:54
-	83	((spacer same (gate electrode))) and (anisotropic\$3 same etch\$3 same spacer)) and ((recess open\$3 hole) same substrate)	EPO; JPO; DERWENT; IBM_TDB	2003/03/06 11:55